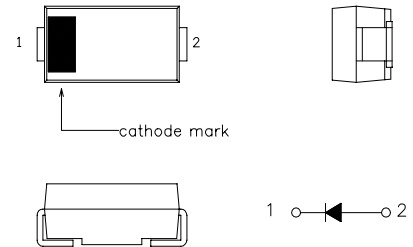


DIODE Type : EC10DS2

FEATURES

- * Miniature Size, Surface Mount Device
- * High Surge Capability
- * Low Forward Voltage Drop
- * Low Reverse Leakage Current
- * Packaged in 12mm Tape and Reel
- * Not Rolling During Assembly

OUTLINE DRAWING



Maximum Ratings

Approx Net Weight:0.06g

Rating	Symbol	EC10DS2			Unit
Repetitive Peak Reverse Voltage	V _{RRM}	200			V
Non-repetitive Peak Reverse Voltage	V _{RSM}	400			V
Average Rectified Output Current	I _O	0.74	Ta=25 °C *1	50Hz Half Sine Wave Resistive Load	A
		1.0	Ta=25 °C *2		
RMS Forward Current	I _{F(RMS)}	1.57			A
Surge Forward Current	I _{FSM}	25	50Hz Half Sine Wave,1cycle Non-repetitive		A
Operating JunctionTemperature Range	T _{jw}	-40 to +150			°C
Storage Temperature Range	T _{stg}	-40 to +150			°C

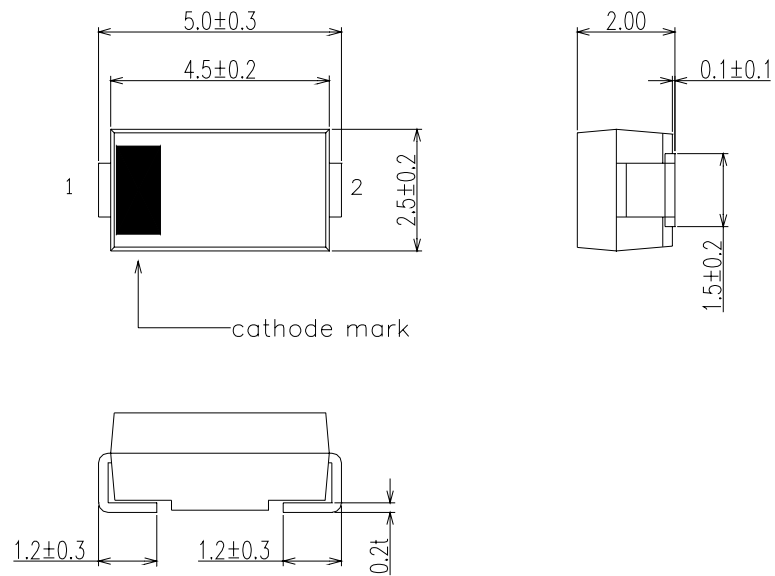
Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j=25\text{ }^{\circ}\text{C}$, $V_{RM}=V_{RRM}$	-	-	10	μA
Peak Forward Voltage	V_{FM}	$T_j=25\text{ }^{\circ}\text{C}$, $I_{FM}=1.0\text{A}$	-	-	1.1	V
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient	*1	-	-	157
			*2	-	-	108

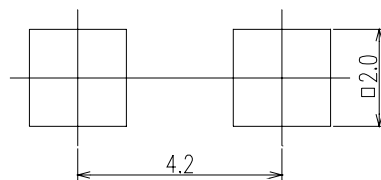
*1 Glass Epoxy Substrate Mounted (Soldering Lands=2x2mm, Both Sides)

*2 Alumina Substrate Mounted (Soldering Lands=2x2mm, Both Sides)

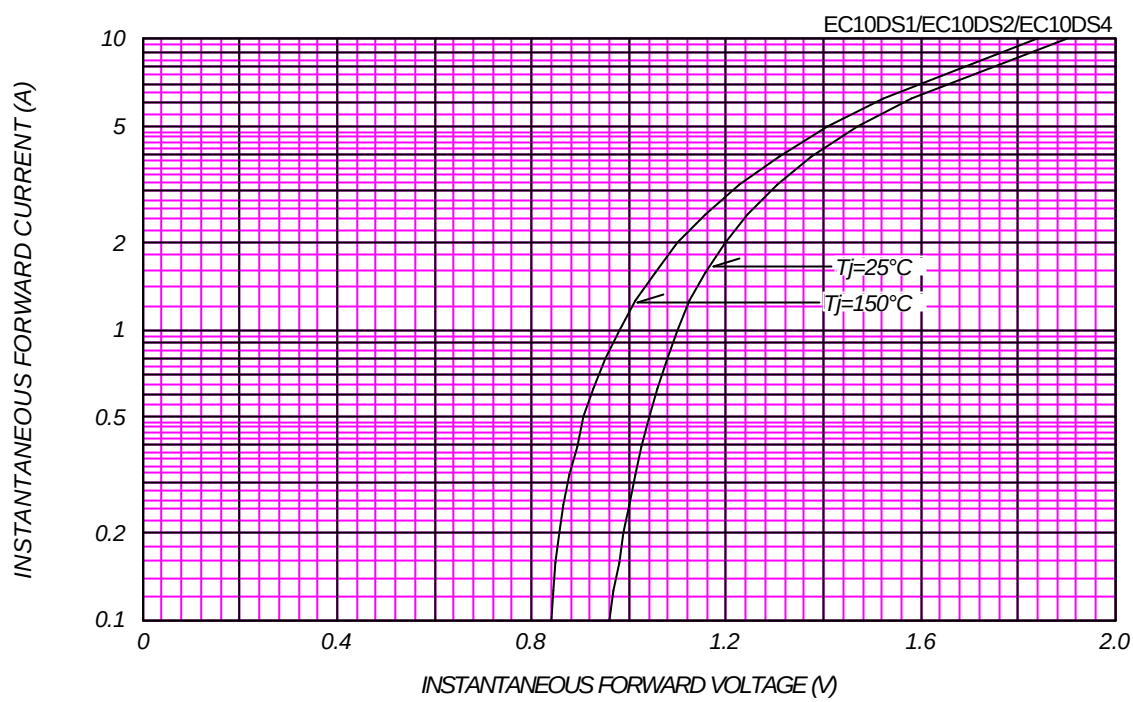
EC10DS2 OUTLINE DRAWING (Dimensions in mm)



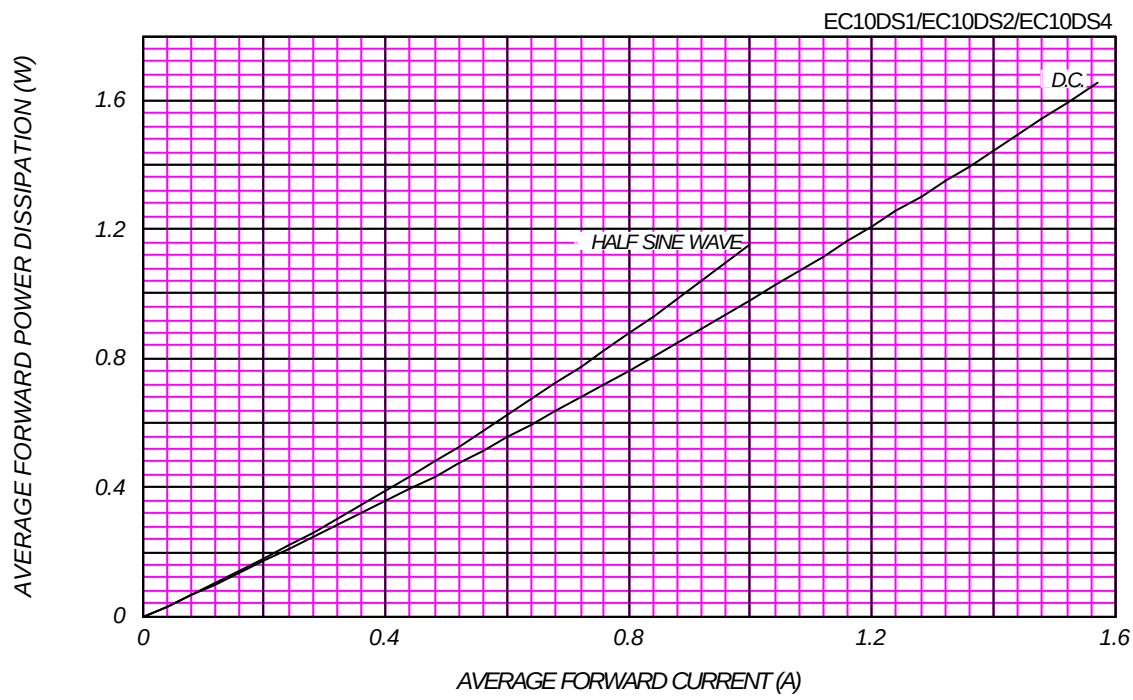
SOLDERING PAD



FORWARD CURRENT VS. VOLTAGE



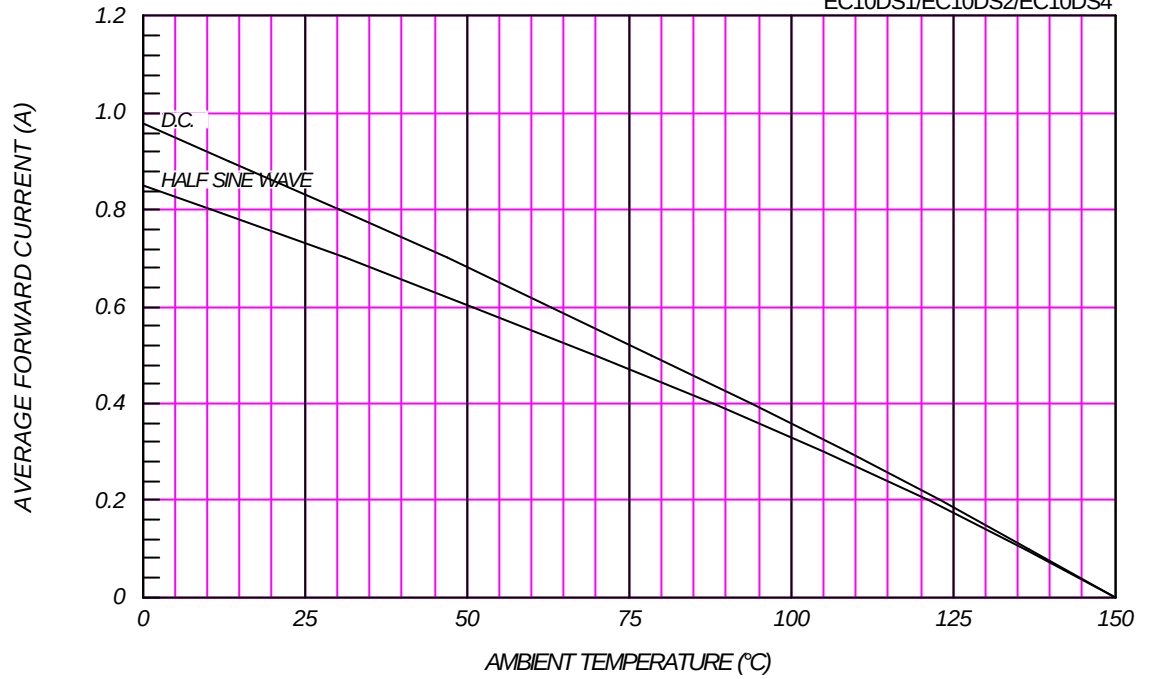
AVERAGE FORWARD POWER DISSIPATION



AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE

Glass-Epoxy Substrate Mounted(Soldering Land=2×2mm)

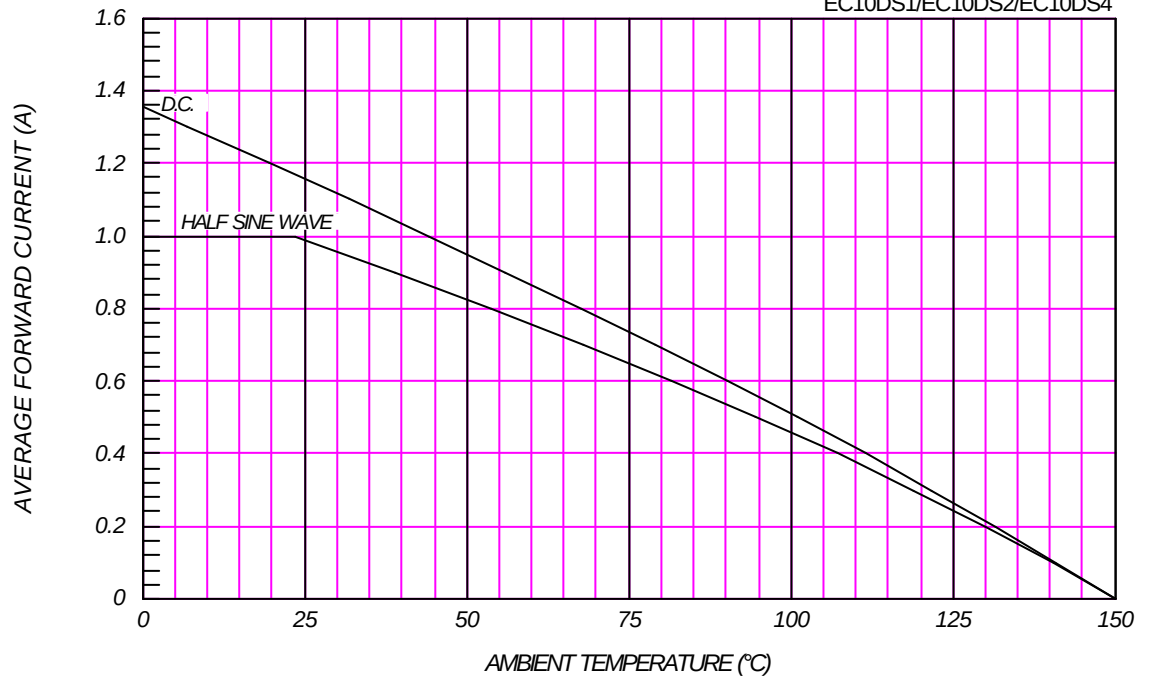
EC10DS1/EC10DS2/EC10DS4



AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE

Alumina Substrate Mounted(Soldering Land=2×2mm)

EC10DS1/EC10DS2/EC10DS4



SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load

EC10DS1/EC10DS2/EC10DS4

